

Harihara Ramamoorthy

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

308
citations

1040056

9
h-index

839539

18
g-index

21
all docs

21
docs citations

21
times ranked

616
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of the high-field transport, Joule-heating-driven conductivity improvement and low-field resistivity behaviour in lightly-reduced free-standing graphene oxide papers. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 245103.	2.8	3
2	Remote Mesoscopic Signatures of Induced Magnetic Texture in Graphene. <i>Physical Review Letters</i> , 2021, 126, 086802.	7.8	0
3	Versatile, Low-Cost, and Portable 2D Material Transfer Setup with a Facile and Highly Efficient DIY Inert-Atmosphere Glove Compartment Option. <i>ACS Omega</i> , 2021, 6, 17952-17964.	3.5	2
4	Exploration of the temperature-dependent correlations present in the structural, morphological and electrical properties of thermally reduced free-standing graphene oxide papers. <i>Journal of Materials Science</i> , 2021, 56, 15134-15150.	3.7	14
5	CVD Synthesis of Intermediate State-Free, Large-Area and Continuous MoS ₂ via Single-Step Vapor-Phase Sulfurization of MoO ₃ Precursor. <i>Nanomaterials</i> , 2021, 11, 2642.	4.1	10
6	Cost-Effective Experimental Setup for Studies of Spin Seebeck Effect and Electrical Transport in Thermoelectric Materials. <i>IEEE Transactions on Instrumentation and Measurement</i> , 2020, 69, 3587-3594.	4.7	3
7	Universal scaling of weak localization in graphene due to bias-induced dispersion decoherence. <i>Scientific Reports</i> , 2020, 10, 5611.	3.3	1
8	Transient Response of h-BN-Encapsulated Graphene Transistors: Signatures of Self-Heating and Hot-Carrier Trapping. <i>ACS Omega</i> , 2019, 4, 4082-4090.	3.5	12
9	In-situ current annealing of graphene-metal contacts. <i>Journal of Physics: Conference Series</i> , 2018, 1144, 012186.	0.4	3
10	Probing charge trapping and joule heating in graphene field-effect transistors by transient pulsing. <i>Semiconductor Science and Technology</i> , 2017, 32, 084005.	2.0	12
11	Negative Differential Conductance & Hot-Carrier Avalanching in Monolayer WS ₂ FETs. <i>Scientific Reports</i> , 2017, 7, 11256.	3.3	18
12	Evaluating the Sources of Graphene's Resistivity Using Differential Conductance. <i>Scientific Reports</i> , 2017, 7, 10317.	3.3	8
13	Conductance fluctuations in graphene in the presence of long-range disorder. <i>Journal of Physics Condensed Matter</i> , 2016, 28, 135302.	1.8	6
14	Thermally Assisted Nonvolatile Memory in Monolayer MoS ₂ Transistors. <i>Nano Letters</i> , 2016, 16, 6445-6451.	9.1	47
15	Freeing Graphene from Its Substrate: Observing Intrinsic Velocity Saturation with Rapid Electrical Pulsing. <i>Nano Letters</i> , 2016, 16, 399-403.	9.1	40
16	Energy relaxation of hot carriers in graphene via plasmon interactions. <i>Journal of Computational Electronics</i> , 2016, 15, 144-153.	2.5	0
17	Plasmon-mediated energy relaxation in graphene. <i>Applied Physics Letters</i> , 2015, 107, 262103.	3.3	3
18	Conduction Mechanisms in CVD-Grown Monolayer MoS ₂ Transistors: From Variable-Range Hopping to Velocity Saturation. <i>Nano Letters</i> , 2015, 15, 5052-5058.	9.1	92

#	ARTICLE	IF	CITATIONS
19	Reversing hot-carrier energy-relaxation in graphene with a magnetic field. Applied Physics Letters, 2014, 104, 193115.	3.3	5
20	Fast Energy Relaxation of Hot Carriers Near the Dirac Point of Graphene. Nano Letters, 2013, 13, 4305-4310.	9.1	29